

Technical Background and general description

Please see the proceedings in the attachment.

Technical details

The descriptions on page 2 to 5 explained the background and the core concept of the method. On the following pages, different embodiments are shown for mechanical fixation as well as for the electrical connection of the Shape Memory Alloy wire.

Fixation of the Free Air Ball

The wire is fed through the bond-capillary of a wire bonder. To allow the pulling of the wire, the tip of the wire must be fixated on the substrate. In this concept, the tip of the wire is deformed, so that the diameter of the wire-tip is larger than the diameter of the remaining wire and the bond capillary. This allows to hook-in the wire tip or to squeeze the wire into squeeze-fit structures in the substrate.

Fel! Hittar inte referenskälla. illustrates one concept shown already in the background paragraphs. A hook-in structure is formed in the substrate (Fel! Hittar inte referenskälla.a), then the Free Air Ball is formed (Fel! Hittar inte referenskälla.b), which is hooked into the structure in the substrate (Fel! Hittar inte referenskälla.c) and allows to pull the SMA wire through the bond capillary (Fel! Hittar inte referenskälla.d).

Another concept is the anchoring using squeeze fit of the Free Air Ball into squeeze-fit structure on the substrate, as schematically illustrated in Figure 2. The SMA wire (201) is fed through the bond capillary (202) and a Free Air Ball (203) is formed. In the substrate (204), a trench (205) is formed with the diameter smaller than the diameter of the Free Air Ball (Figure 2a). The diameter of the Free Air Ball is larger than the diameter of the bond capillary, which allows to squeeze the Free Air Ball into the trench in the substrate (Figure 2b). The tip of the SMA wire is anchored by the squeeze fit of the Free Air Ball into the trench of the substrate (Figure 2c).

As schematically illustrated in Figure 3, the same concept is suitable for squeeze-fit of the Free Air Ball into a V formed trench as for example obtained when etching a silicon substrate with special processes. The SMA wire (301) is fed through the bond capillary (302) and a Free Air Ball (303) is formed. In the substrate (304), a V shaped trench (305) is formed (Figure 3a). The diameter of the Free Air Ball is larger than the diameter of the bond capillary, which allows to squeeze the Free Air Ball into the trench in the substrate (Figure 3b). The tip of the SMA wire is anchored by the squeeze fit of the Free Air Ball into the trench of the substrate (Figure 3c).

Figure 4 schematically illustrates a further variation of the squeeze-fit concept, where deformable clamping structures are formed in the substrate which allow for variations in the SMA wire diameter. The SMA wire (401) is fed through the bond capillary (402) and a Free Air Ball (403) is formed. In the substrate (404), deformable clamp structures (405) are formed (Figure 4a). The diameter of the Free Air Ball is larger than the diameter of the bond capillary, which allows to squeeze the Free Air Ball into the deformable structures in the substrate (Figure 4b). The clamp structures elastically deform during the

squeeze of the Free Air Ball (Figure 4b) and thereby adapt to diameter variations of the SMA wire and hold them in place (Figure 4c).

All the above described concepts schematically illustrated in Figures 2 to 4 are adaptable to enable electrical contacting of the SMA wire at the same time as the mechanical fixation is performed. This allows for a simple contacting and Joule heating of the SMA wire above the conversion temperature. Figures 5 to 7 schematically illustrates the concept. The SMA wire (501, 601, 701) is fed through the bond capillary (502, 602, 702) and a Free Air Ball (503, 603, 703) is formed. On the substrate (504, 604, 704) trenches (505, 605) or deformable clamp structures (705) are formed. Finally, a metal film (506, 606, 706) is deposited onto the substrate (Figures 5a, 6a, 7a). The diameter of the Free Air Ball is larger than the diameter of the bond capillary, which allows to squeeze the Free Air Ball into the trench in the substrate (Figures 5b, 6b, 7b). During the squeezing, the native oxide on the SMA is broken up and the SMA is in direct contact with the metal on the substrate. Thereby, the SMA can be electrically contacted (507, 607, 707) via the metal film (Figure 5c, 6c, 7c).

Instead of using squeeze-fits with and/or without metal liner as illustrated in Figures 2 to 7, the trenches in the substrate can be filled with adhesive to adhesively anchor the Free Air Ball and the wire in the trenches. Figures 8 and 9 schematically illustrate this concept with Figure 8 for straight trenches similar to Figure 2 and Figure 9 for V-shaped trenches similar to Figure 3. The SMA wire (801, 901) is fed through the bond capillary (802, 902) and a Free Air Ball (803, 903) is formed. In the substrate (804, 904), straight (805) or V-shaped trenches (905) are formed, which are then partially filled with adhesive (806, 906) (Figures 8a, 9a). The diameter of the Free Air Ball is larger than the diameter of the bond capillary, which allows to squeeze the Free Air Ball into the adhesive in the trenches in the substrate (Figures 8b, 9b). The Free Air Ball is embedded in adhesive, which is cured (807, 907) and thereby anchors the Free Air Ball (Figures 8c, 9c).

Besides squeeze fit and adhesive anchoring, a snap-in structure can be fabricated to snap the Free Air Ball in to. Figure 10 schematically illustrates this concept. The SMA wire (1001) is fed through the bond capillary (1002) and a Free Air Ball (1003) is formed. In the substrate (1004), a trench (1005) is formed and on top of the substrate a thinner layer is formed (1006) which partially covers the trench (1005) but has an opening in the center of the trench, thereby creating snap-in structures (1007) (Figure 10a). The diameter of the Free Air Ball is larger than the diameter of the bond capillary, which allows to push the Free Air Ball through the opening of the top layer (1006) into the trench in the substrate (Figure 10b). The top layer snaps back (1007) and holds the Free Air Ball in place (Figure 10c).

A variation of the concept schematically illustrated in Figure 10 is to provide a spring in the trench which presses the Free Air Ball against the snap structures in the top layer. Figure 11 schematically illustrates the concept. The SMA wire (1001) is fed through the bond capillary (1002) and a Free Air Ball (1003) is formed. In the substrate (1004), a trench (1005) is formed and on top of the substrate a thinner layer is formed (1006) which partially covers the trench (1005) but has an opening in the center of the trench, thereby creating snap-in structures (1007) (Figure 11a). In the bottom of the trench (1005) a layer (1108) is formed which is elastically deformable. After squeezing the Free Air Ball through the snap-in structures, the Free Air Ball compresses the deformable layer (1108) (Figure 11b). When removing the bond capillary, the elastically deformed layer presses the Free Air Ball into the snap-in structures, which are strong enough to withstand the forces generated by the elastically deformed layer (Figure 11c).

Fixation of the wire

After fixing the tip of the wire with the Free Air Ball, the wire is pulled through the bond capillary and spanned across the substrate to the next clamp structure. In this clamp structure, the wire is clamped and therefore all the concepts shown in Figures 2 to 11 are adaptable.

Figures 12 to 14 schematically illustrate the squeeze fit schemes adapted for squeeze fitting of SMA wires. Using the wire-bonder, the SMA wire (1201, 1301, 1401) is placed above the trench (1202, 1302, 1402) which is formed in the substrate (1203, 1303, 1403) with the diameter smaller than the diameter of the SMA wire (Figures 12a, 13a, 14a). Figure 12 and 13 illustrate squeeze fitting with straight and V-shaped trenches, respectively. Figure 14 is based on the concept shown in Figure 4 and features deformable clamping structures (1405) in the substrate which allow for variations in the SMA wire diameter. The wire is squeezed into the trenches and/or deformable clamping structures using a piston (1204, 1304, 1404), which for example could be a second substrate which is pressed onto the wire and the second substrate in a wafer bonder (Figure 12b, 13b, 14b). The piston is then removed and the wire remains in the trench (Figure 12c, 13c, 14c) following the same principles as in the concepts shown in Figures 2,3,4.

The concepts schematically illustrated in Figures 12 to 14 are adaptable to enable electrical contacting of the SMA wire at the same time as the mechanical fixation is performed. This allows for a simple contacting and Joule heating of the SMA wire above the conversion temperature. Figures 15 to 17 schematically illustrate the concept. The SMA wire (1501, 1601, 1701) is placed above the trench (1502, 1602, 1702) which is formed in the substrate (1503, 1603, 1703) and covered with a metal liner (1504, 1604, 1704). The trench diameter is smaller than the diameter of the SMA wire (Figures 15a, 16a, 17a). Figure 15 and 16 illustrate squeeze fitting with straight and V-shaped trenches, respectively. Figure 17 is based on the concept shown in Figures 4 and 14 and features deformable clamping structures (1707) in the substrate which allow for variations in the SMA wire diameter. The wire is squeezed into the trenches and/or deformable clamping structures using a piston (1505, 1605, 1705), which for example could be a second substrate which is pressed onto the wire and the second substrate in a wafer bonder (Figure 15b, 16b, 17b). During the squeezing, the native oxide on the SMA is broken up and the SMA is in direct contact with the metal on the substrate. Thereby, the SMA can be electrically contacted (1506, 1606, 1706) via the metal film (Figure 15c, 16c, 17c).

The concept with metal liners on the clamp structures shown in Figures 15 to 17 can be enhanced with ball bonds as illustrated in Figure 18. Onto the metal on the final structures of Figures 15 to 17, several Free Air Balls are bonded to mechanically support the clamping of the wires into the clamp structures. The SMA wire (1801) is fed through the bond capillary (1802) and a Free Air Ball (1803) is formed (Figure 18 a,b,c left). The Free Air Ball is bonded onto the clamped wire (1804) and the adjoining metal liner (1805) on the substrate (1806) (Figure 18b). Then, the wire is cut using a high bond energy (1807) (Figure 18c).

Similar to the concepts illustrated in Figures 8 to 9 the trenches in the substrate can be filled with adhesive to adhesively anchor the wire in the trenches. Figures 19 and 20 schematically illustrate this concept with Figure 19 for straight trenches and Figure 20 for V-shaped trenches. The SMA wire (1901, 2001) is placed above the trench/groove (1902, 2002) which is formed in the substrate (1903, 2003) and partially filled with adhesive (1904, 2004) (Figures 19a, 20a). The wire is squeezed into the adhesive in the trenches using a piston (1905, 2005), which for example could be a second substrate which is pressed onto the wire and the second substrate in a wafer bonder (Figures 19b, 20b). Then the wire is embedded in adhesive, which is cured (1906, 2006) and thereby anchors the wire (Figures 19c, 20c).

The adhesive anchoring concept illustrated in Figures 19 and 20 can be combined with adhesive wafer bonding to support the clamping of the wire. Figure 21 illustrates the concept, which is similar for both straight and V-shaped trenches. The SMA wire (2101) is placed above the trench/groove (2102, 2103) which is formed in the substrate (2104) and partially filled with adhesive (2104). The wire is squeezed into the adhesive in the trenches using a second substrate (2105) which is covered with adhesive (2106) and pressed onto the wire and the first substrate (2103). Then, all the adhesive is cured and the wire is anchored both by the adhesive and the second substrate on top. Such an approach is feasible also for the squeeze-fit with metal lined clamp structures. Figure 22 illustrates the concept. The wire (2201) is placed above the metal lined (2202) trench (2203) in the first substrate (2204). The wire is squeezed into the metal lined trenches using a second substrate (2205) which is covered with metal (2206) and pressed onto the wire and the first substrate (2204). Then, the second substrate is bonded with its metal to the metal on the first substrate. Thereby, the SMA can be electrically contacted via the metal film and the clamping is supported by the bonded second substrate.

Similar to the concepts illustrated in Figures 10 and 11, a snap-in structure can be fabricated to snap the wire in to. Figure 23 schematically illustrates this concept. In the substrate (2301), a trench (2302) is formed and on top of the substrate a thinner layer is formed (2303) which partially covers the trench but has an opening in the center of the trench, thereby creating snap-in structures (2304). The SMA wire (2305) is placed above the snap-in structures (Figure 23a). The wire is squeezed through the opening of the top layer into the trench in the substrate using a piston (2306), which for example could be a second substrate which is pressed onto the wire and the second substrate in a wafer bonder (Figure 23b). The top layer snaps back (2307) and holds the wire in place (Figure 23c).

A variation of the concept schematically illustrated in Figure 23 is to provide a spring in the trench which presses the wire against the snap structures in the top layer. Figure 24 schematically illustrates the concept. In the substrate (2401), a trench (2302) is formed and on top of the substrate a thinner layer is formed (2403) which partially covers the trench but has an opening in the center of the trench, thereby creating snap-in structures (2404). In the bottom of the trench a layer (2405) is formed which is elastically deformable (Figure 24a). After squeezing the wire (2406) with the piston (2407) through the snap-in structures, the wire compresses the deformable layer (2408) (Figure 24b). When removing the piston, the elastically deformed layer presses the wire into the snap-in structures, which are strong enough to withstand the forces generated by the elastically deformed layer (Figure 24c).

Process schemes

Figures 25 and 26 show process schemes for the integration of SMA wires using a wire-bonder. The flow in Figure 25 illustrates a process where the first fixation is provided by anchoring the Free Air Ball. Then, all the following fixations required are performed by clamping the wire with the wire-bonder into clamping structures. After the last clamping structure in one line, the wire is cut off by a high energy wedge/stitch bond onto the substrate surface. If necessary, these steps can be repeated to integrate more wires. If not, the wire is integrated and can be further processed.

The flow in Figure 26 illustrates a process where the first fixation is provided by anchoring the Free Air Ball. Then, the wire is spanned over all the clamping structures in the line and finally the wire is cut off by a high energy wedge/stitch bond onto the substrate surface. If necessary, these steps can be repeated to

place more wires. If all wires are in place, they are squeezed into the underlying clamping structures using a piston. If the clamping is strong enough, the substrate can be further processed. If not, additional ball bonds can be placed on the wire in the clamp structures or during the squeezing a second substrate can be bonded onto the wires and the first substrate.

WAFFER-LEVEL INTEGRATION OF NITIT SHAPE MEMORY ALLOY WIRES FOR THE FABRICATION OF MICROACTUATORS USING STANDARD WIRE BONDING TECHNOLOGY

A. C. Fischer, H. Gradin, S. Braun, S. Schröder, G. Stemme and F. Niklaus

KTH – Royal Institute of Technology, Stockholm, Sweden

ABSTRACT

This paper reports on the first integration of SMA wires into silicon based MEMS structures using a standard wire bonder. This approach allows fast and efficient placement, alignment and mechanical attachment of NiTi-based SMA wires to silicon-based MEMS. The wires are mechanically anchored and clamped into deep-etched silicon structures on a wafer. The placement precision is high with an average deviation of 4 μm and the mechanical clamping is strong, allowing successful actuation of the SMA wires.

INTRODUCTION

Shape memory alloy (SMA) is an attractive actuator material to use in microelectromechanical systems (MEMS) when high forces and work are needed. SMA outperforms most other actuation principles at the microscale by more than an order of magnitude because of the high work density that SMAs offer [1]. Traditionally there are mainly two ways of integrating SMA materials into microsystems. The first approach is a pick and place approach where the SMA material and the microsystem is manufactured separately and then combined in a subsequent step [2]. This approach has the advantage of allowing integration of bulk SMA materials, which are commercially available and offered in a wide thickness range at comparably low material cost. However, the SMA integration is performed on a per-device level which results in high assembly cost. The second approach is based on sputter deposition of thin NiTi films directly onto the microstructure [3], which has the benefit of allowing wafer level processing. However, due to a difficult deposition controllability, the process is limited in reproducibility of transformation temperatures and strains and NiTi sputter deposition is mostly feasible for thicknesses of less than 10 μm [4].

Wafer level integration of SMA wires onto silicon microstructures, with the benefit of both wafer level integration and the use of bulk SMA materials, has been shown for microactuators with excellent performance [5]. However, no standardized fabrication process has yet been established or suggested. The placement of the wires requires specially designed tools with manual wire handling, alignment and integration. In contrast, wire bonding is an extremely mature, cost-effective and broadly available backend process for electrical interconnects [6]. It is very attractive to utilize this standard technology due to its very good availability and high performance in terms of reliability, throughput and placement accuracy, with speeds up to 22 bonds per second and placement accuracies within 2 μm . However, direct wire bonding of NiTi SMA wires is not feasible due to the Vickers hard-

ness of the NiTi material, which is one order of magnitude higher [7] as compared to common wire bonding materials such as gold and aluminum. This paper presents the first wafer-level integration concept for NiTi SMA wires onto silicon substrates by using a conventional wire bonding tool.

CONCEPT

Wafer level integration of SMA wires with a wire bonder allows a fast placement and fixation of the wires. No additional alignment step is needed. Because of the hardness of NiTi wires the direct wire bonding of these wires on standard gold or aluminum pads is not feasible. In this paper the wires are instead mechanically fixed by Si clamping and anchor structures on the wafer. These mechanical fixation structures enable the integration of the NiTi wires by using a standard and unmodified wirebonder.

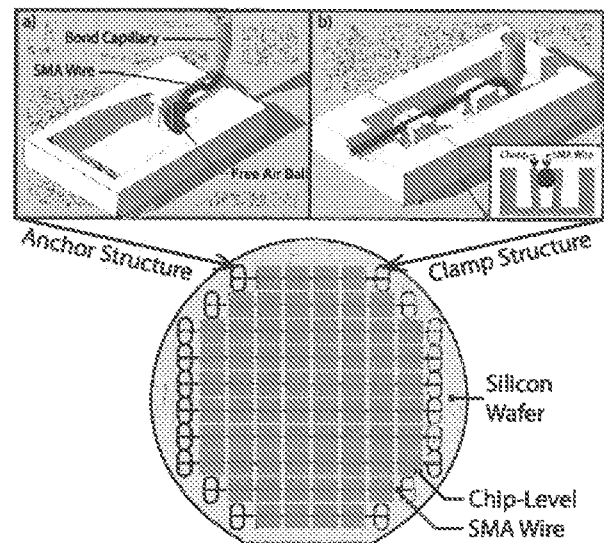


Figure 1: Illustration of the wafer-level integration concept: The SMA wire is mechanically fixated with the help of one anchor and one clamp structure. Each fixation pair is placed on opposite sides of the wafer edge.

The basic integration concept is depicted in Fig. 1. The integration of a SMA wire is separated into wafer- and chip-level integration. Wafer-level integration combines aligning and fixation of a SMA wire on a silicon wafer. The final mechanical and electrical integration can then be performed on chip-level to form the actuator itself.

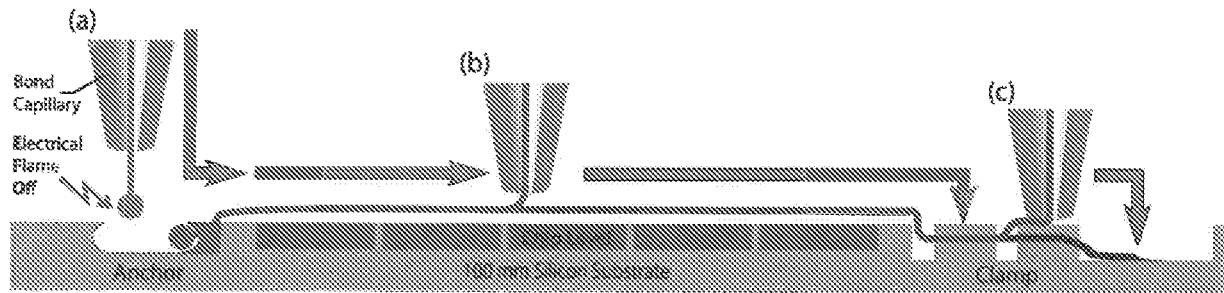


Figure 2: Cross sectional view of the integration flow: First, the free air ball is generated by an electrical discharge (a). The ball is then anchored in its anchoring structure. The SMA wire (37.5 μm diameter) is feeded and guided over the entire wafer area to its second fixation structure (b). The SMA wire is clamped in between silicon cantilevers and finally cut off by truncating the wire by the bond capillary and a high bond force (c).

On wafer-level, the SMA wire is attached using two different mechanical structures in a defined position with high placement accuracy across the entire wafer. Based on a ball-wedge wire bonding process, a free air ball is generated and subsequently anchored in the first integration structure (Fig. 1a). The SMA wire is fixed and can be guided across the wafer towards the clamping structure (Fig. 1b), where the SMA wire is mechanically attached. This wafer-level integration allows in a second step a further attachment also on chip-level. However, the focus of this paper lies on the design and development of the wafer-level integration.

Using this integration concept full wafers can be populated with SMA wires at high placement accuracies. Furthermore using a wire bonder offers high throughput and high reproducibility of the integration process. The complete integration of SMA wires is done at room temperature, thus avoiding the triggering of the SMA transformation, which occurs at elevated temperatures of typically 90 °C. Hence this enables integration of prestrained SMA wires. In addition this integration concept is CMOS compatible, offering the possibility for integrating microelectronic devices with microactuators.

FABRICATION

The wire hooking and clamping structures were fabricated on a 100 mm silicon substrate. Both types of structures are realized by a sequence of anisotropic and isotropic DRIE steps [8]. Etching of both integration structures were performed in a STS ICP etch reactor.

The fabrication of both fixation structures requires one lithography and DRIE process each. The first lithography was performed with standard photoresist, which was applied by spin-coating. The second photoresist application was performed by spray-coating of diluted resist in order to ensure a full protection of the deep-etched structures, which were created by the first DRIE process. As a final step all photoresist residuals were removed by plasma ashing.

The anchor structure, which fixes the start of the wire, is depicted in Fig. 1a and Fig. 3. It consists of two functional

parts, the landing zone and the anchor part. The landing zone enables lowering of the SMA ball into the anchor structure and subsequently fixation into the adjacent anchor part. The etch geometry is crucial for a proper anchoring of the SMA ball. The anchoring of the SMA ball is achieved by a specific undercut etch profile of the anchor structure itself. First an anisotropic trench was etched, followed by a passivation of the vertical sidewalls. Subsequently an isotropic etch creates an undercut underneath the anisotropic etch profile.

The silicon structure for the wire end combines two functional parts, i.e. the clamping structure and the cut off zone. Fig. 1b) and Fig. 4 depicts the clamping structure with a pair of facing vertical cantilevers. Two pairs of facing vertical cantilevers clamp the SMA wire in between them. The first pair fixes and aligns the SMA wire. The second pair stabilizes the SMA wire for the truncation. The anisotropic etch profile of the clamping structure contains a small chamfer in the upper section of the cantilevers, which is realized by a short isotropic etch. The chamfers ensure a constant height of the SMA wire in the clamp, as depicted in Fig. 4.

A semi-automatic wire-bonder (Delvotec 5410) was used to integrate the wires. A commercially available pre-strained NiTi SMA wire (Flexinol®, 37.5 μm in diameter) with a transformation temperature of 90 °C was used. Because the wire was already prestrained, no special tool for prestraining the wires was needed [5]. The wire integration, depicted in Fig. 2, starts with forming a free air ball caused by an electrical discharge, which locally melts the wire on the tip of the bond capillary. The liquid metal at the end of the SMA wire rolls up and forms a free air ball. The Electrical Flame Off (EFO) is performed in helium atmosphere, since the TiNi alloys tend to oxidize in air during rapid melting by glow discharges [10]. The free air ball is then lowered into the landing zone and subsequently hooked into its adjacent anchoring part. By utilizing the wire bonder, the SMA wire is placed over the wafer to the clamping structure where it is pushed in between pairs of facing cantilevers. Finally, the SMA wire is cut off by truncating the wire with the bond capillary and a high bond force. This integration approach for SMA wires

opens a wide range of different integration methods on chip-level, which can then be used for manufacturing of high performance actuators with for example polymer fixation [5], or by using the clamp structures to fixate SMA wires also on individual chips.

EXPERIMENTAL RESULTS

Fig. 3 depicts an anchor structure, that was fabricated by combined anisotropic and isotropic deep reactive ion etching in three subsequent steps. Both the underetched (out of plane) sidewall structure and the tapered (in-plane) design safely fixings the SMA wire with its anchor. This design is very forgiving towards unequally formed and/or sized free air balls and thus ensures a reliable anchoring of the SMA wire.

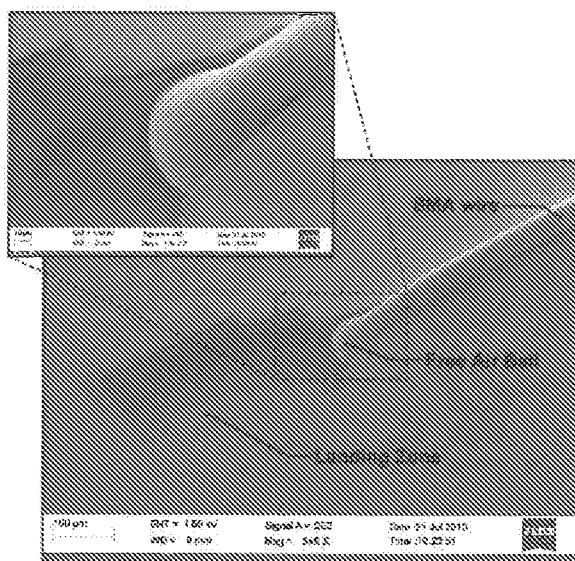


Figure 3: SEM image of an anchor structure, that was fabricated by combined anisotropic and isotropic deep reactive ion etching in three steps.

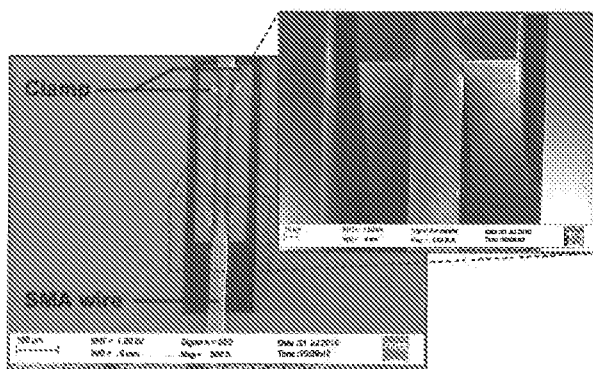


Figure 4: SEM image of a clamp fixation with a magnified view on one clamp feature. The wire is pushed in between the facing pair of cantilevers with the help of the wire bonder. Four similar clamps are used for the fixation of each wire.

Clamping structures with cantilever dimensions of $50 \times 500 \times 220 \mu\text{m}$, as depicted in Fig. 4, fixed the SMA wire mechanically most stable. A force of xxx mN was necessary to snap the wire into the clamp structure.

The final step of the wire integration is the wire truncation, which was performed analog to a stitch bond. However, the use of a very high bond force of xxx mN and ultrasonics result in a straight cut of the wire and in contrast to conventional wire bonding not in a deformation and micro weld of the wire to the surface, as depicted in Fig. 5. This indicates also that it is not feasible to fix SMA wires by the means of traditional wire bonding.

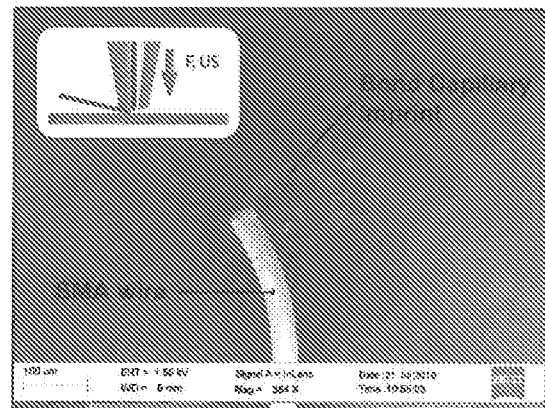


Figure 5: SEM image of a truncated SMA wire. The use of a high bond force and ultrasonics result in a straight cut of the wire and in contrast to conventional wire bonding not in a deformation and micro weld of the wire to the surface.

The presented wafer-level integration method also comprises the alignment of the SMA wire on chip-level. The placement accuracy of this integration method was analysed with an optical profilometer (Wyko NT9300). As depicted in Fig. 6, both the in-plane wire placement deviation from the ideal geometrical anchor-to-clamp center line and the distance from the wire to the substrate (i.e. chip-level) was determined. The sample, a 75 mm long SMA wire with a diameter of 37.5 μm was integrated on a 100 mm silicon substrate. The in-plane average deviation is 4.19 ± 4.22 (σ) μm with a maximum of 13.9 μm . The out-of-plane distance of the SMA wire to the substrate is in average 15.6 ± 4.5 (σ) μm and maximal 23.2 μm (Fig. 6). This is an important measure for the design of the chip-level fixation of the SMA wire, which could e.g. be performed with Ni-electroplating in a subsequent step [9]. In addition, a basic evaluation of the mechanical robustness of the anchor and clamp structures was performed by implementing a simple actuator. This actuator is based on a 300 μm thick silicon cantilever with a length of 100 mm and a width of 2 mm as cold state reset and two parallel integrated 75 mm long SMA wires as actuation. The energy input is provided by a hotplate on which the actuator is fixed on one side to enhance the thermal contact. Fig. 7a) illustrates the cross-

section of the actuator both in actuated and idle position. Fig. 7b) depict the actuator in a semi and Fig. 7c) in fully actuated state. It reveals that both SMA wire fixation elements withstand the force that is generated by the SMA wires, which is 200 mN according to the wire data sheet [11]. The actuation was performed several hundred times without failure.

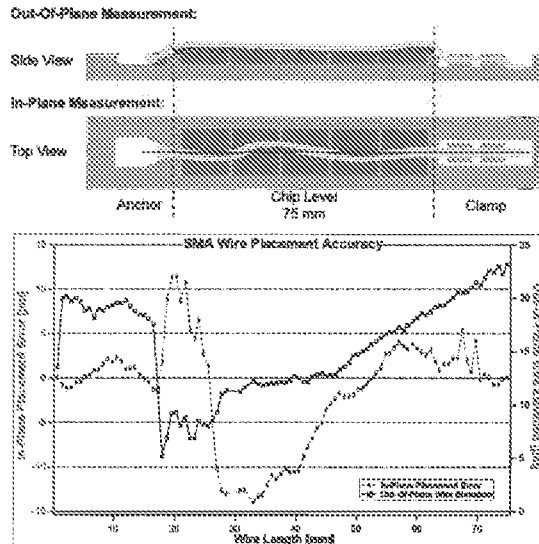


Figure 6: White Light Interferometric measurement data for the alignment accuracy of a SMA wire with a length of 75 mm and a diameter of 37.5 μm . As indicated in the drawing, the out-of-plane measurement (blue straight graph) determines the distance between the wire and the substrate, the in-plane measurement (red dashed graph) determines the lateral wire placement deviation from an ideal geometrical anchor-to-clamp center line.

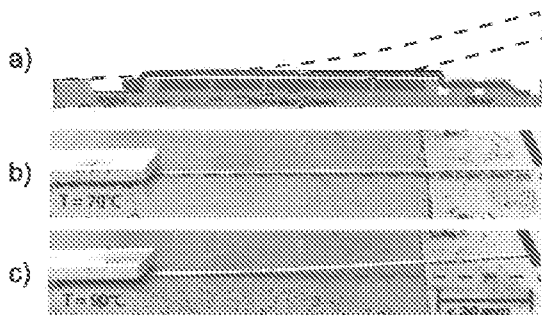


Figure 7: In order to verify the mechanical stability of the presented wire fixation approach, two 75 mm long SMA wires have been integrated in parallel on a silicon chip with a size of 3×100 mm. a) drawing of a cross-section, the red dashed outline represents the chip in a hot state. b) shows an image of a slightly actuated device on a hotplate with a temperature of 70 °C. c) device with increased actuation at 90 °C.

DISCUSSION AND CONCLUSIONS

We have successfully demonstrated wafer level integration of shape memory alloy wires using standard wire bonder equipment. Even though the SMA wire integration was performed with a semi-automatic wire bonder an excellent placement accuracy could be achieved in this work. The usage of fully automated wire bonding equipment with optical pattern recognition and alignment systems potentially further improve these results and enables the implementation of this technique for mass production. The anchoring and clamping of SMA wire showed an excellent robustness, which indicates the applicability of this integration concept also on chip-/actuator-level.

ACKNOWLEDGEMENTS

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Claims

1. Method to attach a wire to a substrate, characterized in that said wire is mechanically attached into a 3D structures on said substrate.
2. Device comprising a wire attached to a substrate, characterized in that said wire is mechanically attached into a 3D structure on said substrate.